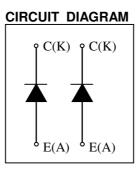
#### DIODE MODULE

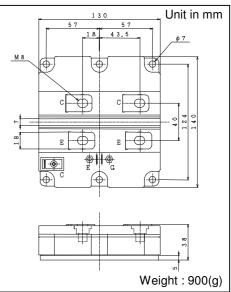
# MDM900E45A

### PRELIMINARY SPEC.

#### FEATURES

- \* Low noise due to soft and fast recovery diodes.
- \* High reliability, high durability diodes.
- \* Isolated heat sink(terminal to base).





#### ABSOLUTE MAXIMUM RATINGS (TC=25°C)

			,			
Item			Symbol	Unit	MDM900E45A	
Repetitive Peak Reverse Voltage			V <sub>RRM</sub>	V	4,500	
Forward Current		DC	l <sub>F</sub>	Α	900	
		1ms	I <sub>FM</sub>	Π	1,800	
Junction Temperature			Tj	°C	-40 $\sim$ +125	
Storage Temperature			Tstg	⊃°C	-40 $\sim$ +125	(1)
Isolation Test Voltage	Terminals-base		V <sub>ISO</sub>	V <sub>RMS</sub>	6,000 (AC 1 minute)	
	Terminal 1-Terminal 2		V <sub>ISO T-T</sub>	V RMS	6,000 (AC 1 minute)	
Screw Torque	Terminals (M8)		-	N∙m	15	(2)
	Mounting (M6)		-		6	(3)
Notool (1) Tarres			al the state of the state of the state	to make a which a loss of the		

Notes: (1) Terminal temperature shall not exceed the spepecified temperture in any operation. (2) Recommended Value  $15^{+0}/_{3}$ N·m (3) Recommended Value  $5.5\pm0.5$ N·m

#### **ELECTRICAL CHARECTERISTICS**

Item	Symbol	Unit	Min.	Тур.	Max.	Test Conditions
Repetitive Reverse Current	I <sub>RRM</sub>	mA	-	20	40.0	VAK=4,500V, Tj=125°C
Forward Voltage Drop	V <sub>F</sub>	V	3.3	4.5	tbd	IF=900A, Tj=125°C
Reverse Recovery Time	trr	μs	-	0.6		V <sub>CC</sub> =2,600V, Ic=900A, L=130nH
Reverse Recovery Loss	E <sub>rr(10%)</sub>	J/P	-	1.1	tbd	$Tj=125^{\circ}C Rg=2.2 \Omega$ (4)

#### **PACKAGE CHARECTERISTICS**

Item	Symbol	Unit	Min.	Тур.	Max.	Test Conditions	
Terminal Resistance	RCE	mΩ	-	0.3	-		
Terminal Stray Inductance	LSCE	nH	-	35	-		
Thermal Impedance	Rth(j-c)	°C/W	-	-	0.017	Junction to case	
Comparative tracking index	CTI		-	600	-		
Contact Thermal Impedance	Rth(c-f)	°C/W	-	0.008	-	Case to fin per module	
Base Plate material			AI-SiC				
Insulation substrate material			AIN				

Notes:(4) Counter arm; MBN900D45A VGE=+/-15V

 $R_G$  value is the test condition's value for evaluation of the switching times, not recommended value. Please, determine the suitable  $R_G$  value after the measurement of switching waveforms (overshoot voltage, etc.) with appliance mounted.

\* Please contact our representatives at order.

\* For improvement, specifications are subject to change without notice.

\* For actual application, please confirm this spec sheet is the newest revision.

#### **OUTLINE DRAWING**

# **HITACHI POWER SEMICONDUCTORS**

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